Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	1584
Total RAM Bits	18432
Number of I/O	157
Number of Gates	60000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	201-VFBGA, CSBGA
Supplier Device Package	201-CSP (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/aglp060v5-cs201i

Each I/O module contains several input, output, and output enable registers.

Hot-swap (also called hot-plug, or hot-insertion) is the operation of hot-insertion or hot-removal of a card in a powered-up system.

Cold-sparing (also called cold-swap) refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Wide Range I/O Support

IGLOO PLUS devices support JEDEC-defined wide range I/O operation. IGLOO PLUS devices support both the JESD8-B specification, covering 3 V and 3.3 V supplies, for an effective operating range of 2.7 V to 3.6 V, and JESD8-12 with its 1.2 V nominal, supporting an effective operating range of 1.14 V to 1.575 V.

Wider I/O range means designers can eliminate power supplies or power conditioning components from the board or move to less costly components with greater tolerances. Wide range eases I/O bank management and provides enhanced protection from system voltage spikes, while providing the flexibility to easily run custom voltage applications.

Specifying I/O States During Programming

You can modify the I/O states during programming in FlashPro. In FlashPro, this feature is supported for PDB files generated from Designer v8.5 or greater. See the *FlashPro User's Guide* for more information.

Note: PDB files generated from Designer v8.1 to Designer v8.4 (including all service packs) have limited display of Pin Numbers only.

1. Load a PDB from the FlashPro GUI. You must have a PDB loaded to modify the I/O states during programming.
2. From the FlashPro GUI, click PDB Configuration. A FlashPoint – Programming File Generator window appears.
3. Click the Specify I/O States During Programming button to display the Specify I/O States During Programming dialog box.
4. Sort the pins as desired by clicking any of the column headers to sort the entries by that header. Select the I/Os you wish to modify (Figure 1-4 on page 1-8).
5. Set the I/O Output State. You can set Basic I/O settings if you want to use the default I/O settings for your pins, or use Custom I/O settings to customize the settings for each pin. Basic I/O state settings:

   1 – I/O is set to drive out logic High

   0 – I/O is set to drive out logic Low

   Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming Z -Tri-State: I/O is tristated

2 – IGLOO PLUS DC and Switching Characteristics

General Specifications

Operating Conditions

Stresses beyond those listed in Table 2-1 may cause permanent damage to the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Absolute Maximum Ratings are stress ratings only; functional operation of the device at these or any other conditions beyond those listed under the Recommended Operating Conditions specified in Table 2-2 on page 2-2 is not implied.

Table 2-1 • **Absolute Maximum Ratings**

Symbol	Parameter	Limits	Units
VCC	DC core supply voltage	–0.3 to 1.65	V
VJTAG	JTAG DC voltage	–0.3 to 3.75	V
VPUMP	Programming voltage	–0.3 to 3.75	V
VCCPLL	Analog power supply (PLL)	–0.3 to 1.65	V
VCCI	DC I/O buffer supply voltage	–0.3 to 3.75	V
V_I[1]	I/O input voltage	–0.3 V to 3.6 V	V
T_{STG}[2]	Storage temperature	–65 to +150	°C
T_J[2]	Junction temperature	+125	°C

Notes:

1. *The device should be operated within the limits specified by the datasheet. During transitions, the input signal may undershoot or overshoot according to the limits shown in Table 2-4 on page 2-3.*
2. *For flash programming and retention maximum limits, refer to Table 2-3 on page 2-3, and for recommended operating limits, refer to Table 2-2 on page 2-2.*

Calculating Power Dissipation

Quiescent Supply Current

Quiescent supply current (I_{DD}) calculation depends on multiple factors, including operating voltages (VCC, VCCI, and VJTAG), operating temperature, system clock frequency, and power mode usage. Microsemi recommends using the Power Calculator and SmartPower software estimation tools to evaluate the projected static and active power based on the user design, power mode usage, operating voltage, and temperature.

Table 2-8 • **Power Supply State per Mode**

Modes/Power Supplies	Power Supply Configurations				
	VCC	VCCPLL	VCCI	VJTAG	VPUMP
Flash*Freeze	On	On	On	On	On/off/floating
Sleep	Off	Off	On	Off	Off
Shutdown	Off	Off	Off	Off	Off
No Flash*Freeze	On	On	On	On	On/off/floating

Note: Off: Power Supply level = 0 V

Table 2-9 • **Quiescent Supply Current (IDD) Characteristics, IGLOO PLUS Flash*Freeze Mode***

	Core Voltage	AGLP030	AGLP060	AGLP125	Units
Typical (25°C)	1.2 V	4	8	13	µA
	1.5 V	6	10	18	µA

*Note: *IDD includes VCC, VPUMP, VCCI, VJTAG, and VCCPLL currents.*

Table 2-10 • **Quiescent Supply Current (IDD) Characteristics, IGLOO PLUS Sleep Mode***

ICCI Current	Core Voltage	AGLP030	AGLP060	AGLP125	Units
VCCI = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	µA
VCCI = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	µA
VCCI = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	µA
VCCI = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	µA
VCCI = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	µA

*Note: *IDD = N_{BANKS} * ICCI*

Table 2-11 • **Quiescent Supply Current (IDD) Characteristics, IGLOO PLUS Shutdown Mode**

	Core Voltage	AGLP030	AGLP060	AGLP125	Units
Typical (25°C)	1.2 V / 1.5 V	0	0	0	µA

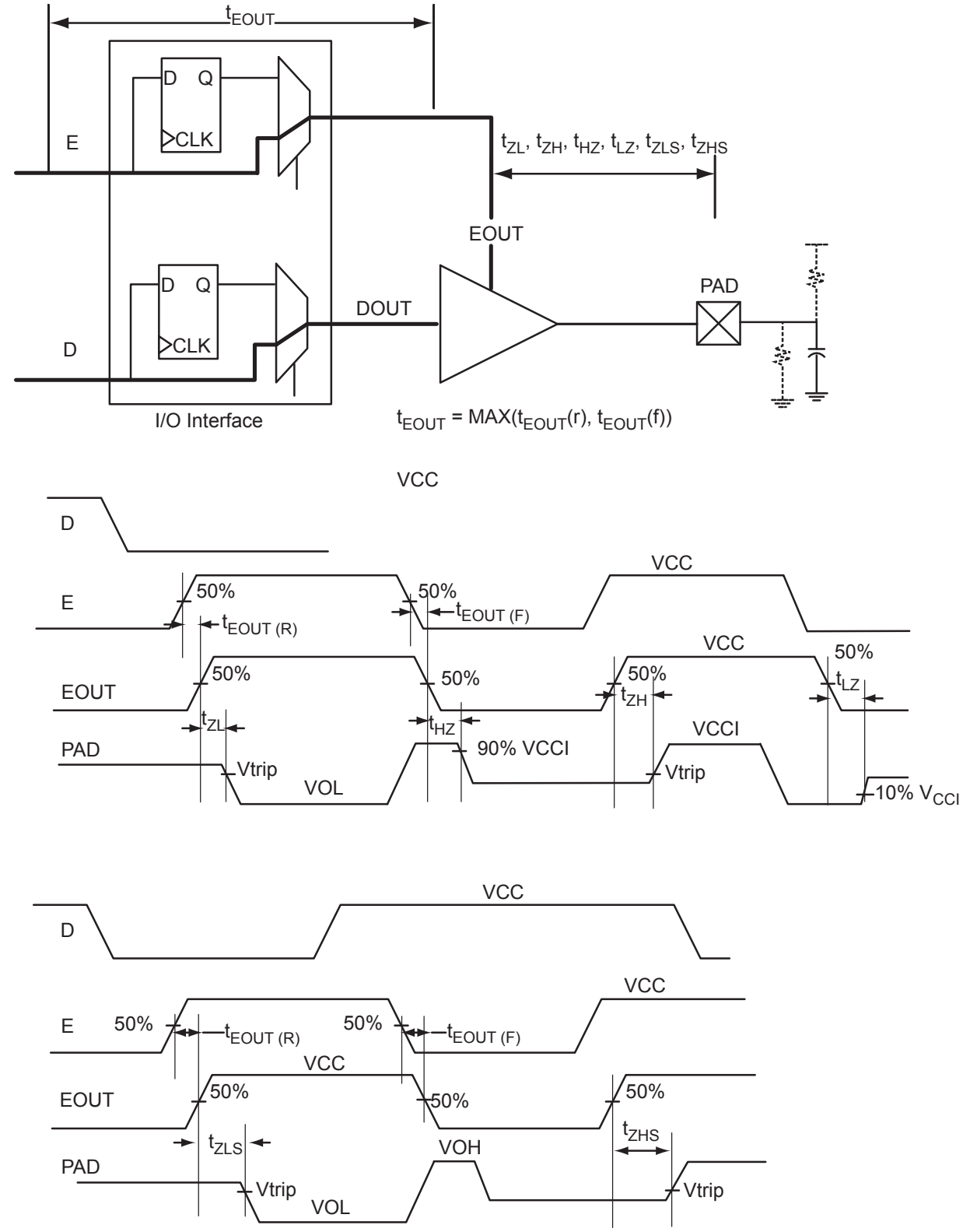

Figure 2-6 • **Tristate Output Buffer Timing Model and Delays (example)**

Table 2-22 • Summary of Maximum and Minimum DC Input Levels Applicable to Commercial and Industrial Conditions

	Commercial[1]		Industrial[2]	
	IIL[3]	IIH[4]	IIL[3]	IIH[4]
DC I/O Standards	µA	µA	µA	µA
3.3 V LVTTL / 3.3 V LVCMOS	10	10	15	15
3.3 V LVCMOS Wide Range	10	10	15	15
2.5 V LVCMOS	10	10	15	15
1.8 V LVCMOS	10	10	15	15
1.5 V LVCMOS	10	10	15	15
1.2 V LVCMOS[5]	10	10	15	15
1.2 V LVCMOS Wide Range[5]	10	10	15	15

Notes:

1. *Commercial range (0°C < T_A < 70°C)*
2. *Industrial range (–40°C < T_A < 85°C)*
3. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
4. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
5. *Applicable to IGLOO PLUS V2 devices operating at VCCI ³ VCC.*

Summary of I/O Timing Characteristics – Default I/O Software Settings

Table 2-23 • Summary of AC Measuring Points

Standard	Measuring Trip Point (Vtrip)
3.3 V LVTTL / 3.3 V LVCMOS	1.4 V
3.3 V LVCMOS Wide Range	1.4 V
2.5 V LVCMOS	1.2 V
1.8 V LVCMOS	0.90 V
1.5 V LVCMOS	0.75 V
1.2 V LVCMOS	0.60 V
1.2 V LVCMOS Wide Range	0.60 V

Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings, STD Speed Grade
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[1]	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY})	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	5 pF	–	0.98	2.31	0.19	0.99	1.37	0.67	2.34	1.86	2.65	3.38	ns
3.3 V LVCMOS Wide Range[2]	100 µA	12 mA	High	5 pF	–	0.98	3.21	0.19	1.32	1.92	0.67	3.21	2.52	3.73	4.73	ns
2.5 V LVCMOS	12 mA	12 mA	High	5 pF	–	0.98	2.29	0.19	1.19	1.40	0.67	2.32	1.94	2.65	3.27	ns
1.8 V LVCMOS	8 mA	8 mA	High	5 pF	–	0.98	2.45	0.19	1.12	1.61	0.67	2.48	2.16	2.71	3.16	ns
1.5 V LVCMOS	4 mA	4 mA	High	5 pF	–	0.98	2.71	0.19	1.26	1.80	0.67	2.75	2.39	2.78	3.15	ns
1.2 V LVCMOS	2 mA	2 mA	High	5 pF	–	0.98	3.38	0.19	1.57	2.34	0.67	3.26	2.78	2.99	3.24	ns
1.2 V LVCMOS Wide Range[3]	100 µA	2 mA	High	5 pF	–	0.98	3.38	0.19	1.57	2.34	0.67	3.26	2.78	2.99	3.24	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
3. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.*
4. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-36 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.97	3.94	0.18	0.85	1.15	0.66	4.02	3.46	1.82	1.87	ns
4 mA	STD	0.97	3.94	0.18	0.85	1.15	0.66	4.02	3.46	1.82	1.87	ns
6 mA	STD	0.97	3.20	0.18	0.85	1.15	0.66	3.27	2.94	2.04	2.27	ns
8 mA	STD	0.97	3.20	0.18	0.85	1.15	0.66	3.27	2.94	2.04	2.27	ns
12 mA	STD	0.97	2.72	0.18	0.85	1.15	0.66	2.78	2.57	2.20	2.53	ns
16 mA	STD	0.97	2.72	0.18	0.85	1.15	0.66	2.78	2.57	2.20	2.53	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-37 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.97	2.36	0.18	0.85	1.15	0.66	2.41	1.90	1.82	1.98	ns
4 mA	STD	0.97	2.36	0.18	0.85	1.15	0.66	2.41	1.90	1.82	1.98	ns
6 mA	STD	0.97	1.96	0.18	0.85	1.15	0.66	2.01	1.56	2.04	2.38	ns
8 mA	STD	0.97	1.96	0.18	0.85	1.15	0.66	2.01	1.56	2.04	2.38	ns
12 mA	STD	0.97	1.76	0.18	0.85	1.15	0.66	1.80	1.39	2.20	2.64	ns
16 mA	STD	0.97	1.76	0.18	0.85	1.15	0.66	1.80	1.39	2.20	2.64	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray.*

Applies to 1.2 V DC Core Voltage

Table 2-38 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	4.56	0.19	0.99	1.37	0.67	4.63	3.98	2.26	2.57	ns
4 mA	STD	0.98	4.56	0.19	0.99	1.37	0.67	4.63	3.98	2.26	2.57	ns
6 mA	STD	0.98	3.80	0.19	0.99	1.37	0.67	3.96	3.45	2.49	2.98	ns
8 mA	STD	0.98	3.80	0.19	0.99	137	0.67	3.86	3.45	2.49	2.98	ns
12 mA	STD	0.98	3.31	0.19	0.99	1.37	0.67	3.36	3.07	2.65	3.25	ns
16 mA	STD	0.98	3.31	0.19	0.99	1.37	0.67	3.36	3.07	2.65	3.25	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-39 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	2.92	0.19	0.99	1.37	0.67	2.97	2.38	2.25	2.70	ns
4 mA	STD	0.98	2.92	0.19	0.99	1.37	0.67	2.97	2.38	2.25	2.70	ns
6 mA	STD	0.98	2.52	0.19	0.99	1.37	0.67	2.56	2.03	2.49	3.11	ns
8 mA	STD	0.98	2.52	0.19	0.99	1.37	0.67	2.56	2.03	2.49	3.11	ns
12 mA	STD	0.98	2.31	0.19	0.99	1.37	0.67	2.34	1.86	2.65	3.38	ns
16 mA	STD	0.98	2.31	0.19	0.99	1.37	0.67	2.34	1.86	2.65	3.38	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray*

3.3 V LVCMOS Wide Range

Table 2-40 • Minimum and Maximum DC Input and Output Levels

3.3 V LVCMOS Wide Range	Equivalent Software Default Drive Strength Option[1]	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
Drive Strength		Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	µA	µA	Max. µA[4]	Max. µA[4]	µA[5]	µA[5]
100 µA	2 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	4 mA	–0.3	0.8	2	3.6	0.4	VDD – 0.2	100	100	25	27	10	10
100 µA	6 mA	–0.3	0.8	2	3.6	0.4	VDD – 0.2	100	100	51	54	10	10
100 µA	8 mA	–0.3	0.8	2	3.6	0.4	VDD – 0.2	100	100	51	54	10	10
100 µA	12 mA	–0.3	0.8	2	3.6	0.4	VDD – 0.2	100	100	103	109	10	10
100 µA	16 mA	–0.3	0.8	2	3.6	0.4	VDD – 0.2	100	100	103	109	10	10

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < V CCI. Input current is larger when operating outside recommended ranges.*
4. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
5. *Currents are measured at 85°C junction temperature.*
6. *Software default selection highlighted in gray.*

Table 2-41 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	3.3	1.4	5

*Note: *Measuring point = Vtrip. See Table 2-23 on page 2-20 for a complete table of trip points.*

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-54 • 1.8 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.97	5.89	0.18	1.00	1.43	0.66	6.01	5.43	1.78	1.30	ns
4 mA	STD	0.97	4.82	0.18	1.00	1.43	0.66	4.92	4.56	2.08	2.08	ns
6 mA	STD	0.97	4.13	0.18	1.00	1.43	0.66	4.21	3.96	2.30	2.46	ns
8 mA	STD	0.97	4.13	0.18	1.00	1.43	0.66	4.21	3.96	2.30	2.46	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-55 • 1.8 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.97	2.82	0.18	1.00	1.43	0.66	2.88	2.78	1.78	1.35	ns
4 mA	STD	0.97	2.30	0.18	1.00	1.43	0.66	2.35	2.11	2.08	2.15	ns
6 mA	STD	0.97	2.00	0.18	1.00	1.43	0.66	2.04	1.76	2.29	2.55	ns
8 mA	STD	0.97	2.00	0.18	1.00	1.43	0.66	2.04	1.76	2.29	2.55	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray.*

Applies to 1.2 V DC Core Voltage

Table 2-56 • 1.8 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	6.43	0.19	1.12	1.61	0.67	6.54	5.93	2.19	1.88	ns
4 mA	STD	0.98	5.33	0.19	1.12	1.61	0.67	5.41	5.03	2.50	2.68	ns
6 mA	STD	0.98	4.61	0.19	1.12	1.61	0.67	4.69	4.41	2.72	3.07	ns
8 mA	STD	0.98	4.61	0.19	1.12	1.61	0.67	4.69	4.41	2.72	3.07	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-57 • 1.8 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	3.30	0.19	1.12	1.61	0.67	3.34	3.21	2.19	1.93	ns
4 mA	STD	0.98	2.76	0.19	1.12	1.61	0.67	2.79	2.51	2.50	2.76	ns
6 mA	STD	0.98	2.45	0.19	1.12	1.61	0.67	2.48	2.16	2.71	3.16	ns
8 mA	STD	0.98	2.45	0.19	1.12	1.61	0.67	2.48	2.16	2.71	3.16	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray.*

1.2 V DC Core Voltage

Table 2-77 • Output Data Register Propagation Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	1.03	ns
t_{OSUD}	Data Setup Time for the Output Data Register	0.52	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	1.22	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	1.31	ns
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	0.24	ns
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	0.24	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.19	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.19	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width High for the Output Data Register	0.31	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width Low for the Output Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

Output Enable Register

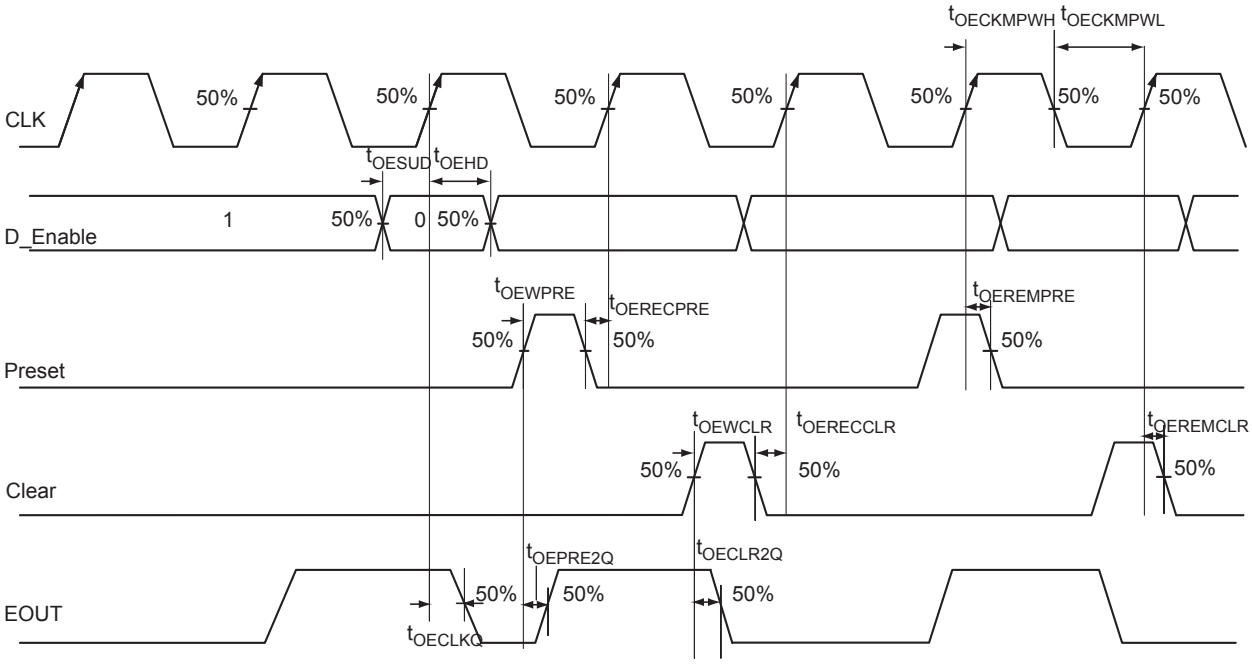

Figure 2-16 • **Output Enable Register Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-78 • **Output Enable Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.68	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.33	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	0.84	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	0.91	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.24	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.24	ns
t_{OEWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.19	ns
t_{OEWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.31	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Timing Characteristics

1.5 V DC Core Voltage

Table 2-80 • Combinatorial Cell Propagation Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Combinatorial Cell	Equation	Parameter	Std.	Units
INV	Y = !A	t_{PD}	0.72	ns
AND2	Y = A · B	t_{PD}	0.86	ns
NAND2	Y = !(A · B)	t_{PD}	1.00	ns
OR2	Y = A + B	t_{PD}	1.26	ns
NOR2	Y = !(A + B)	t_{PD}	1.16	ns
XOR2	Y = A ⊕ B	t_{PD}	1.46	ns
MAJ3	Y = MAJ(A, B, C)	t_{PD}	1.47	ns
XOR3	Y = A ⊕ B ⊕ C	t_{PD}	2.12	ns
MUX2	Y = A !S + B S	t_{PD}	1.24	ns
AND3	Y = A · B · C	t_{PD}	1.40	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V DC Core Voltage

Table 2-81 • Combinatorial Cell Propagation Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Combinatorial Cell	Equation	Parameter	Std.	Units
INV	Y = !A	t_{PD}	1.26	ns
AND2	Y = A · B	t_{PD}	1.46	ns
NAND2	Y = !(A · B)	t_{PD}	1.78	ns
OR2	Y = A + B	t_{PD}	2.47	ns
NOR2	Y = !(A + B)	t_{PD}	2.17	ns
XOR2	Y = A ⊕ B	t_{PD}	2.62	ns
MAJ3	Y = MAJ(A, B, C)	t_{PD}	2.66	ns
XOR3	Y = A ⊕ B ⊕ C	t_{PD}	3.77	ns
MUX2	Y = A !S + B S	t_{PD}	2.20	ns
AND3	Y = A · B · C	t_{PD}	2.49	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

1.2 V DC Core Voltage

***Table 2-83* • Register Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{CLKQ}	Clock-to-Q of the Core Register	1.61	ns
t_{SUD}	Data Setup Time for the Core Register	1.17	ns
t_{HD}	Data Hold Time for the Core Register	0.00	ns
t_{SUE}	Enable Setup Time for the Core Register	1.29	ns
t_{HE}	Enable Hold Time for the Core Register	0.00	ns
t_{CLR2Q}	Asynchronous Clear-to-Q of the Core Register	0.87	ns
t_{PRE2Q}	Asynchronous Preset-to-Q of the Core Register	0.89	ns
t_{REMCLR}	Asynchronous Clear Removal Time for the Core Register	0.00	ns
t_{RECCLR}	Asynchronous Clear Recovery Time for the Core Register	0.24	ns
t_{REMPRE}	Asynchronous Preset Removal Time for the Core Register	0.00	ns
t_{RECPRE}	Asynchronous Preset Recovery Time for the Core Register	0.24	ns
t_{WCLR}	Asynchronous Clear Minimum Pulse Width for the Core Register	0.46	ns
t_{WPRE}	Asynchronous Preset Minimum Pulse Width for the Core Register	0.46	ns
t_{CKMPWH}	Clock Minimum Pulse Width High for the Core Register	0.95	ns
t_{CKMPWL}	Clock Minimum Pulse Width Low for the Core Register	0.95	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

Table 2-95 • RAM512X18
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	1.28	ns
t_{AH}	Address hold time	0.25	ns
t_{ENS}	REN, WEN setup time	1.13	ns
t_{ENH}	REN, WEN hold time	0.13	ns
t_{DS}	Input data (WD) setup time	1.10	ns
t_{DH}	Input data (WD) hold time	0.55	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	6.56	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	2.67	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address – applicable to opening edge	0.29	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address – applicable to opening edge	0.36	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow through)	3.21	ns
	RESET Low to data out Low on RD (pipelined)	3.21	ns
$t_{REMRSTB}$	RESET removal	0.93	ns
$t_{RECRSTB}$	RESET recovery	4.94	ns
$t_{MPWRSTB}$	RESET minimum pulse width	1.18	ns
t_{CYC}	Clock cycle time	10.90	ns
F_{MAX}	Maximum frequency	92	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Special Function Pins

NC **No Connect**

This pin is not connected to circuitry within the device. These pins can be driven to any voltage or can be left floating with no effect on the operation of the device.

DC **Do Not Connect**

This pin should not be connected to any signals on the PCB. These pins should be left unconnected.

Packaging

Semiconductor technology is constantly shrinking in size while growing in capability and functional integration. To enable next-generation silicon technologies, semiconductor packages have also evolved to provide improved performance and flexibility.

Microsemi consistently delivers packages that provide the necessary mechanical and environmental protection to ensure consistent reliability and performance. Microsemi IC packaging technology efficiently supports high-density FPGAs with large-pin-count Ball Grid Arrays (BGAs), but is also flexible enough to accommodate stringent form factor requirements for Chip Scale Packaging (CSP). In addition, Microsemi offers a variety of packages designed to meet your most demanding application and economic requirements for today's embedded and mobile systems.

Related Documents

IGLOO PLUS Device Family User's Guide

http://www.microsemi.com/soc/documents/IGLOOPLUS_UG.pdf

The following documents provide packaging information and device selection for low power flash devices.

Product Catalog

http://www.microsemi.com/soc/documents/ProdCat_PIB.pdf

Lists devices currently recommended for new designs and the packages available for each member of the family. Use this document or the datasheet tables to determine the best package for your design, and which package drawing to use.

Package Mechanical Drawings

http://www.microsemi.com/soc/documents/PckgMechDrwngs.pdf

This document contains the package mechanical drawings for all packages currently or previously supplied by Microsemi. Use the bookmarks to navigate to the package mechanical drawings.

Additional packaging materials are available at
http://www.microsemi.com/soc/products/solutions/package/docs.aspx.

CS289	
Pin Number	AGLP030 Function
A1	IO03RSB0
A2	NC
A3	NC
A4	GND
A5	IO10RSB0
A6	IO14RSB0
A7	IO16RSB0
A8	IO18RSB0
A9	GND
A10	IO23RSB0
A11	IO27RSB0
A12	NC
A13	NC
A14	GND
A15	NC
A16	NC
A17	IO30RSB0
B1	IO01RSB0
B2	GND
B3	NC
B4	NC
B5	IO07RSB0
B6	NC
B7	VCCIB0
B8	IO17RSB0
B9	IO19RSB0
B10	IO24RSB0
B11	IO28RSB0
B12	VCCIB0
B13	NC
B14	NC
B15	NC
B16	IO31RSB0
B17	GND
C1	NC
C2	IO00RSB0
C3	IO04RSB0

CS289	
Pin Number	AGLP030 Function
C4	NC
C5	VCCIB0
C6	IO09RSB0
C7	IO13RSB0
C8	IO15RSB0
C9	IO21RSB0
C10	GND
C11	IO29RSB0
C12	NC
C13	NC
C14	NC
C15	GND
C16	IO34RSB0
C17	NC
D1	NC
D2	IO119RSB3
D3	GND
D4	IO02RSB0
D5	NC
D6	NC
D7	NC
D8	GND
D9	IO20RSB0
D10	IO25RSB0
D11	NC
D12	NC
D13	GND
D14	IO32RSB0
D15	IO35RSB0
D16	NC
D17	NC
E1	VCCIB3
E2	IO114RSB3
E3	IO115RSB3
E4	IO118RSB3
E5	IO05RSB0
E6	NC

CS289	
Pin Number	AGLP030 Function
E7	IO06RSB0
E8	IO11RSB0
E9	IO22RSB0
E10	IO26RSB0
E11	VCCIB0
E12	NC
E13	IO33RSB0
E14	IO36RSB1
E15	IO38RSB1
E16	VCCIB1
E17	NC
F1	IO111RSB3
F2	NC
F3	IO116RSB3
F4	VCCIB3
F5	IO117RSB3
F6	NC
F7	NC
F8	IO08RSB0
F9	IO12RSB0
F10	NC
F11	NC
F12	NC
F13	NC
F14	GND
F15	NC
F16	IO37RSB1
F17	IO41RSB1
G1	IO110RSB3
G2	GND
G3	IO113RSB3
G4	NC
G5	NC
G6	NC
G7	GND
G8	GND
G9	VCC

Revision	Changes	Page
Revision 13 (June 2012)	Figure 2-30 • FIFO Read and Figure 2-31 • FIFO Write have been added (SAR 34843).	2-73
	Updated the terminology used in Timing Characteristics in the following tables: Table 2-96 • FIFO and Table 2-97 • FIFO (SAR 38236).	2-76
	The following sentence was removed from the "VMVx I/O Supply Voltage (quiet)" section in the "Pin Descriptions and Packaging" section: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with “Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks” (SAR 38320). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1
Revision 12 (March 2012)	The "In-System Programming (ISP) and Security" section and "Security" section were revised to clarify that although no existing security measures can give an absolute guarantee, Microsemi FPGAs implement the best security available in the industry (SAR 34664).	I, 1-2
	The Y security option and Licensed DPA Logo were added to the "IGLOO PLUS Ordering Information" section. The trademarked Licensed DPA Logo identifies that a product is covered by a DPA counter-measures license from Cryptography Research (SAR 34724).	III
	The "Specifying I/O States During Programming" section is new (SAR 34695).	1-7
	The following sentence was removed from the "Advanced Architecture" section: "In addition, extensive on-chip programming circuitry allows for rapid, single-voltage (3.3 V) programming of IGLOO PLUS devices via an IEEE 1532 JTAG interface" (SAR 34684).	1-3

Revision	Changes	Page
Revision 11 (continued)	Table 2-2 • Recommended Operating Conditions[1,2] was revised. 1.2 V DC wide range supply voltage and 3.3 V wide range supply voltage (SAR 26270) were added for VCCI. VJTAG DC Voltage was revised (SAR 24052). The value range for VPUMP programming voltage for operation was changed from "0 to 3.45" to "0 to 3.6" (SAR 25220).	2-2
	Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.425 V) and Table 2-7 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.14 V) were revised.	2-6, 2-6
	Table 2-8 • Power Supply State per Mode is new.	2-7
	The tables in the "Quiescent Supply Current" section were updated (SARs 24882 and 24112). Some of the table notes were changed or deleted.	2-7
	VIH maximum values in tables were updated as needed to 3.6 V (SARs 20990, 79370).	N/A
	The values in the following tables were updated. 3.3 V LVCMOS and 1.2 V LVCMOS wide range were added to the tables where applicable. Table 2-13 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings Table 2-14 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings[1] Table 2-21 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings Table 2-22 • Summary of Maximum and Minimum DC Input Levels Table 2-23 • Summary of AC Measuring Points Table 2-25 • Summary of I/O Timing Characteristics—Software Default Settings, STD Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings, STD Speed Grade Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V Table 2-28 • I/O Output Buffer Maximum Resistances [1]	2-9 2-9 2-19 2-20 2-20 2-22 2-23 2-24
	A table note was added to Table 2-16 • Different Components Contributing to the Static Power Consumption in IGLOO PLUS Devices and Table 2-18 • Different Components Contributing to the Static Power Consumption in IGLOO PLUS Devices stating the value for PDC4 is the minimum contribution of the PLL when operating at lowest frequency.	2-10, 2-11
	Table 2-29 • I/O Weak Pull-Up/Pull-Down Resistances was revised, including addition of 3.3 V and 1.2 V LVCMOS wide range. The notes defining $R_{WEAK\ PULL\text{-}UP\text{-}MAX}$ and $R_{WEAK\ PULLDOWN\text{-}MAX}$ were revised (SAR 21348).	2-25
	Table 2-30 • I/O Short Currents IOSH/IOSL was revised to include data for 3.3 V and 1.2 V LVCMOS wide range (SAR 79353 and SAR 79366).	2-25
	Table 2-31 • Duration of Short Circuit Event before Failure was revised to change the maximum temperature from 110°C to 100°C, with an example of six months instead of three months (SAR 26259).	2-26

Revision	Changes	Page
Revision 11 (continued)	The tables in the "Single-Ended I/O Characteristics" section were updated. Notes clarifying IIL and IIH were added. Tables for 3.3 V LVCMOS and 1.2 V LVCMOS wide range were added (SAR 79370, SAR 79353, and SAR 79366). Notes in the wide range tables state that the minimum drive strength for any LVCMOS 3.3 V (or LVCMOS 1.2 V) software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 25700).	2-27
	The following sentence was deleted from the "2.5 V LVCMOS" section: It uses a 5 V–tolerant input buffer and push-pull output buffer (SAR 24916).	2-32
	The tables in the "Input Register" section, "Output Register" section, and "Output Enable Register" section were updated. The tables in the "VersaTile Characteristics" section were updated.	2-45 through 2-56
	The following tables were updated in the "Global Tree Timing Characteristics" section: Table 2-85 • AGLP060 Global Resource (1.5 V) Table 2-86 • AGLP125 Global Resource (1.5 V) Table 2-88 • AGLP060 Global Resource (1.2 V)	2-58
	Table 2-90 • IGLOO PLUS CCC/PLL Specification and Table 2-91 • IGLOO PLUS CCC/PLL Specification were revised (SAR 79388). VCO output jitter and maximum peak-to-peak jitter data were changed. Three notes were added to the table in connection with these changes.	2-61
	Figure 2-28 • Write Access after Write onto Same Address and Figure 2-29 • Write Access after Read onto Same Address were deleted.	N/A
	The tables in the "SRAM", "FIFO" and "Embedded FlashROM Characteristics" sections were updated.	2-68, 2-78

Revision	Changes	Page
Revision 3 (continued)	The table note for Table 2-9 • Quiescent Supply Current (IDD) Characteristics, IGLOO PLUS Flash*Freeze Mode* to remove the sentence stating that values do not include I/O static contribution.	2-7
	The table note for Table 2-10 • Quiescent Supply Current (IDD) Characteristics, IGLOO PLUS Sleep Mode* was updated to remove VJTAG and VCCI and the statement that values do not include I/O static contribution.	2-7
	The table note for Table 2-11 • Quiescent Supply Current (IDD) Characteristics, IGLOO PLUS Shutdown Mode was updated to remove the statement that values do not include I/O static contribution.	2-7
	Note 2 of Table 2-12 • Quiescent Supply Current (IDD), No IGLOO PLUS Flash*Freeze Mode 1 was updated to include VCCPLL. Table note 4 was deleted.	2-8
	Table 2-13 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings and Table 2-14 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings[1] were updated to remove static power. The table notes were updated to reflect that power was measured on VCC_I. Table note 2 was added to Table 2-13 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings.	2-9, 2-9
	Table 2-16 • Different Components Contributing to the Static Power Consumption in IGLOO PLUS Devices and Table 2-18 • Different Components Contributing to the Static Power Consumption in IGLOO PLUS Devices were updated to change the definition for P_{DC5} from bank static power to bank quiescent power. Table subtitles were added for Table 2-16 • Different Components Contributing to the Static Power Consumption in IGLOO PLUS Devices, Table 2-17 • Different Components Contributing to Dynamic Power Consumption in IGLOO PLUS Devices, and Table 2-18 • Different Components Contributing to the Static Power Consumption in IGLOO PLUS Devices.	2-10, 2-11
	The "Total Static Power Consumption—P_{STAT}" section was revised.	2-12
	Table 2-32 • Schmitt Trigger Input Hysteresis is new.	2-26
Packaging v1.3	The "CS281" package drawing is new.	4-13
	The "CS281" table for the AGLP125 device is new.	4-13
Revision 3 (continued)	The "CS289" package drawing was incorrect. The graphic was showing the CS281 mechanical drawing and not the CS289 mechanical drawing. This has now been corrected.	4-17
Revision 2 (Jun 2008) Packaging v1.2	The "CS289" table for the AGLP030 device is new.	4-17
Revision 1 (Jun 2008) Packaging v1.1	The "CS289" table for the AGLP060 device is new.	4-20
	The "CS289" table for the AGLP125 device is new.	4-23